

# SANYO Semiconductors DATA SHEET

N-Channel Silicon MOSFET

# EMH1402 — General-Purpose Switching Device **Applications**

## **Features**

- · Low ON-resistance.
- · 4V drive.

# **Specifications**

# Absolute Maximum Ratings at Ta=25°C

Parameter	Symbol	Conditions	Ratings	Unit
Drain-to-Source Voltage	VDSS		30	V
Gate-to-Source Voltage	VGSS		±20	V
Drain Current (DC)	ID		6	Α
Drain Current (Pulse)	IDP	PW≤10μs, duty cycle≤1%	24	Α
Allowable Power Dissipation	PD	Mounted on a ceramic board (1200mm <sup>2</sup> X0.8mm)	1.5	W
Channel Temperature	Tch		150	°C
Storage Temperature	Tstg		-55 to +150	°C

### Electrical Characteristics at Ta=25°C

Parameter	Symbol	Conditions	Ratings			Unit
			min	typ	max	Unit
Drain-to-Source Breakdown Voltage	V(BR)DSS	I <sub>D</sub> =1mA, V <sub>GS</sub> =0V	30			V
Zero-Gate Voltage Drain Current	IDSS	VDS=30V, VGS=0V			1	μΑ
Gate-to-Source Leakage Current	IGSS	V <sub>GS</sub> =±16V, V <sub>DS</sub> =0V			±10	μΑ
Cutoff Voltage	VGS(off)	V <sub>DS</sub> =10V, I <sub>D</sub> =1mA	1.2		2.6	V
Forward Transfer Admittance	yfs	V <sub>DS</sub> =10V, I <sub>D</sub> =3A	2.9	4.9		S
Static Drain-to-Source On-State Resistance	R <sub>DS</sub> (on)1	I <sub>D</sub> =3A, V <sub>G</sub> S=10V		21	28	mΩ
	R <sub>DS</sub> (on)2	I <sub>D</sub> =1.5A, V <sub>G</sub> S=4.5V		35	49	mΩ
	RDS(on)3	ID=1.5A, VGS=4V		41	58	mΩ
Input Capacitance	Ciss	V <sub>DS</sub> =10V, f=1MHz		740		pF
Output Capacitance	Coss	V <sub>DS</sub> =10V, f=1MHz		140		pF
Reverse Transfer Capacitance	Crss	V <sub>DS</sub> =10V, f=1MHz		120		pF
Turn-ON Delay Time	t <sub>d</sub> (on)	See specified Test Circuit.		11.0		ns
Rise Time	tr	See specified Test Circuit.		50		ns
Turn-OFF Delay Time	t <sub>d</sub> (off)	See specified Test Circuit.		62		ns
Fall Time	tf	See specified Test Circuit.		45		ns

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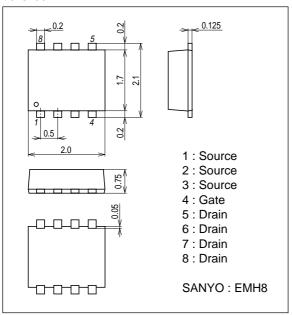
# EMH1402

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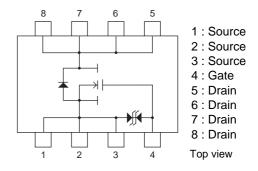
Parameter	Symbol	Conditions	Ratings			Unit
			min	typ	max	J OIN
Total Gate Charge	Qg	V <sub>DS</sub> =10V, V <sub>GS</sub> =10V, I <sub>D</sub> =6A		14.5		nC
Gate-to-Source Charge	Qgs	V <sub>DS</sub> =10V, V <sub>GS</sub> =10V, I <sub>D</sub> =6A		2.3		nC
Gate-to-Drain "Miller" Charge	Qgd	V <sub>DS</sub> =10V, V <sub>GS</sub> =10V, I <sub>D</sub> =6A		2.6		nC
Diode Forward Voltage	VSD	IS=6A, VGS=0V		0.83	1.2	V

# **Package Dimensions**

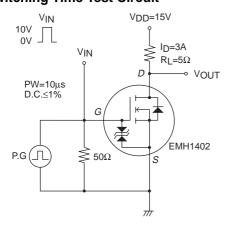
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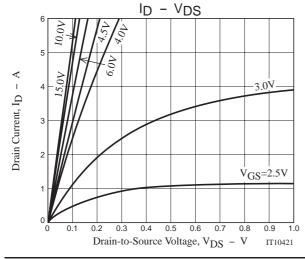


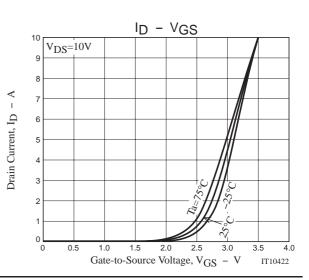
# **Electrical Connection**

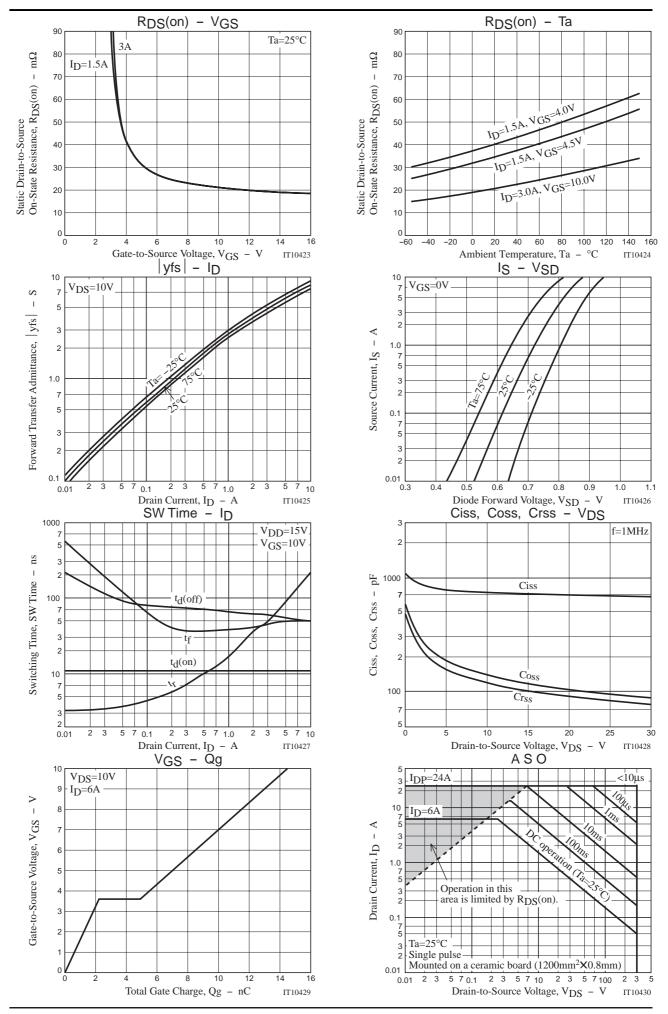


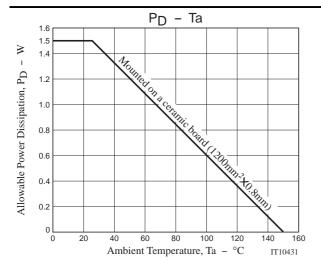
# **Switching Time Test Circuit**











Note on usage: Since the EMH1402 is a MOSFET product, please avoid using this device in the vicinity of highly charged objects.

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